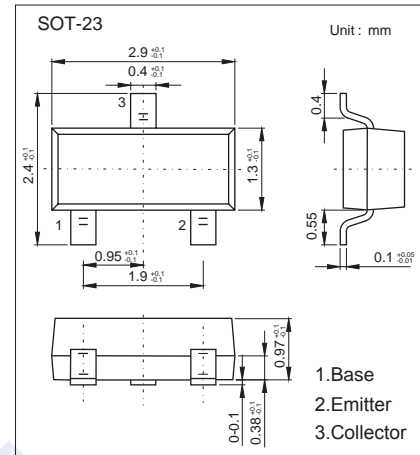


PNP Transistors

2KB4019

■ Features

- High Voltage
- High Transition Frequency
- Complementary to 2KD3010

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-100	V
Collector - Emitter Voltage	V_{CE0}	-100	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-800	mA
Base Current	I_B	-100	
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -1\text{mA}, I_E = 0$	-100			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -10\text{mA}, I_B = 0$	-100			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -1\text{mA}, I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -100\text{V}, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -500\text{mA}$			-1	
DC current gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$	100		300	
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			30	pF
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$		120		MHz

■ Marking

Marking	21
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■ Typical Characteristics

